

## ABSTRACT

A method of forming an integrated circuit with a semiconductor substrate is provided. A gate dielectric is formed on the semiconductor substrate, and a gate is formed on the gate dielectric. A raised source/drain layer is formed on the semiconductor substrate adjacent the gate and the gate dielectric. An amorphized shallow source/drain extension implanted region is formed in the raised source/drain layer and the semiconductor substrate therebeneath. The amorphized region is then recrystallized to form a shallow source/drain extension having residual recrystallization damage elevated into the raised source/drain layer.